

Amendment to the Specification:

Rewrite the second paragraph on page 1 to read as follows:

This application is related to Patent Application Serial Number 10/670,037 ~~xxx,xxx~~ (Attorney Docket Number TI-33719, filed simultaneously with this patent application) entitled "High Capacitive Density Stacked Decoupling Capacitor Structure"; Patent Application Serial Number 10/335,333 (Attorney Docket Number TI-34155, filed 12/31/02) entitled "MIM Capacitors and Methods for Fabricating Same"; Patent Application Serial Number 10/638,596 (Attorney Docket Number TI-34155.1, filed 08/11/03) entitled "MIM Capacitors and Methods for Fabricating Same"; and ~~Patent Application Serial Number 10/xxx,xxx (Attorney Docket Number TI-35260, filed xx/xx/xx) entitled "Capacitor Integration at Top Metal Level With a Protective Cladding for Copper Surface Protection"~~. With their mention in this section, these patent applications are not admitted to be prior art with respect to the present invention.

Rewrite the first paragraph on page 6 to read as follows:

In the best mode application, the top electrode includes a first layer of TiN 100 and a second, strap layer of TaN 110. Depending on the process technique used to create the capacitor dielectric 90, the top electrode may also contain impurities (*i.e.*, carbon, hydrogen, and nitrogen). The top electrode strap layer 110 is TaN in the best mode application because it is compatible with copper processes and it acts as an effective barrier to the out-diffusion of copper from the metal lines 30b into the capacitor dielectric. The top electrode first layer 100 is comprised of TiN in the best mode application to take advantage of the higher capacitance density obtained with a TiN/TaO<sub>x</sub> interface as opposed to a TaN/TaO<sub>x</sub> interface. However, the use of the TiN first layer 100 is optional, as shown in FIG. 1B and described more fully below.